L Number	Hits	Search Text	DB	Time stamp
- Number	0	substrate and "amorphous silicon" and "optical layer" and reflect\$8 and (laser	USPAT; US-PGPUB;	2004/09/16
		near4 anneal\$4) and molten and crystal\$8 and polysilicon	EPO; JPO; DERWENT	
_	73	substrate and "amorphous silicon" and optical and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 12:35
_	2	• •	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 12:48
-	94	·	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 12:49
-	54	_	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 12:49
_	24		USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 12:50
	0	substrate and "amorphous silicon" and optical and "silicon nitride" and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon and (pattern near4 mask) and "anisotropic etch"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 12:51
	7	substrate and "amorphous silicon" and optical and "silicon nitride" and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon and (pattern near4 mask) and "anisotropic"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 12:52
_	6	substrate and "amorphous silicon" and optical and "silicon nitride" and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon and (pattern near4 mask) and "anisotropic" and "silicon oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 12:52